

## ABSTRACT OF DISCLOSURE

A solid image capturing element comprising a plurality of vertical shift registers arranged to each correspond to a column  
5 of a plurality of light receiving pixels in a matrix arrangement,  
a horizontal shift register provided on an output side of the  
plurality of vertical shift registers, and an output section  
provided on an output side of the horizontal shift register. In  
this solid image capturing element, a reverse conductive  
10 semiconductor region is formed over one major surface of one  
conductive semiconductor substrate, the plurality of light  
receiving pixels, the plurality of vertical shift registers, the  
horizontal shift register, and the output section are formed in  
the semiconductor region, and a portion of the semiconductor region  
15 where the output section is formed has a higher dopant concentration  
than the portion of the semiconductor region where the horizontal  
shift register is formed.